

In the Specification:

On page 1, between the title and the first line, please insert the following new paragraph:

This is a divisional of application Serial No. 10/080,108, filed February 21, 2002, which is a divisional of Serial No. 09/005,176 filed January 8, 1998, now U.S. Patent No. 6,406,946, which is a continuation of Serial No. 08/669,272 filed May 29, 1996, now U.S. Patent No. 5,742,074.

Please replace the paragraph beginning on page 29, line 25, with the following rewritten paragraph:

~~Bumps 28b~~ Bumps are formed on the ends of the even number-th drain bus lines 16b on the upper end as viewed in FIG. 9. The bumps 28b are commonly connected to the drain connection line 34b through thin connection lines 36b.

Please replace the paragraph beginning on page 41, line 18, with the following rewritten paragraph:

On the transparent insulating substrate 10, the gate connection line 24b and the thin connection lines ~~26b~~<sup>26a</sup> of the same layer as the metal layer 46 are formed. On the metal layer 46, the first insulating film 48 is formed. On the ~~first~~<sup>first</sup> insulating film 48, the

gate connection line 24a of the same layer as the semiconductor active layer 50 and the metal layer 52 is formed. The second insulating film 54 is formed on the first insulating film 54 and the gate connection line 24a. The contact holes 27a are formed in the second insulating film 54 and reach the gate connection line 24a. The contact holes 27b are formed in the first and the second insulating films 48, 54 and reach the thin connection lines 26a. On the second insulating film 54, the connection line 25 of the same layer as the transparent electrode film 56 is formed and interconnects the thin connection lines 26a and the gate connection line 24b through the contact holes 27a, 27b.